

FQD12N20L

Power MOSFET, N-Channel, Logic Level, QFET®, 200 V, 9.0 A, 280 mΩ, DPAK

Product Overview

For complete documentation, see the data sheet.

This N-Channel enhancement mode power MOSFET is produced using a proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 9A, 200V, RDS(on) = 280mΩ (Max.) @VGS = 10 V, ID = 4.5A
- Low gate charge (Typ. 16nC)
- Low Crss (Typ. 17pF)
- 100% avalanche tested
- Low level gate drive requirement allowing direct operation from logic drivers

Applications

- LED TV
- CRT/RPTV
- AC-DC Merchant Power Supply - Servers & Workstations
- Workstation
- Server & Mainframe

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{DS(BR) Min} (V)	V _{GS Max} (V)	V _{GS(th) Max} (V)	I _{D Max} (A)	P _{D Max} (W)	R _{DS(on) Max} @ V _{GS} = 2.5 V (mΩ)	R _{DS(on) Max} @ V _{GS} = 4.5 V (mΩ)	R _{DS(on) Max} @ V _{GS} = 10 V (mΩ)	Q _{g Typ} @ V _{GS} = 4.5 V (nC)	Q _{g Typ} @ V _{GS} = 10 V (nC)	C _{iss Typ} (pF)	Package Type
FQD12N20LTM	0.3245		Active	N-Channel	Single	200	±30	2	9	55	-	320	280	-	16	830	DPAK-3 / TO-252-3